

<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>				ATTY DOCKET NO. FIS9-2001-029 SUS3		SERIAL NO. <u>100-807629</u> <u>10/047,964</u>		
				Tze-Chiang Chen et al.				
				FILING <u>3/23/04</u> <u>01/15/2002</u>		GROUP <u>2925</u>		
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
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CL		6,043,152	03/28/2000	Chang et al.				
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							YES	NO
CL		WO 00/19523	06/06/2000	CA,CN,JP, European Patent				
		JP2001015480A	01/19/2001	Japan				
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CL		Soo Geun Lee et al., "Low Dielectric Constant 3MS a-SiC:H as Cu Diffusion Barrier Layer in Cu Dual Damascene Process," Japanese Journal of Applied Physics, Part 1, Vol. 40, No. 4B, pp. 2663-2668, April 2001.						
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

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ATTY DOCKET NO.  
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Tze-Chiang Chen et al.

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*catomlee*

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8.30.04

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